

IN THE CLAIMS

1. A semiconductor integrated circuit having nonvolatile memory cells each of which comprises one memory transistor, two switch transistors and two diffusion-layer lines, wherein said memory transistor includes a gate insulating film having discrete traps and a memory gate electrode connected to a word line, said two diffusion-layer lines constitute a source line and a bit line, and the switch gate electrodes of said two switch transistors are extended along said source line and said bit line.

2-14. Canceled.